

AON4703

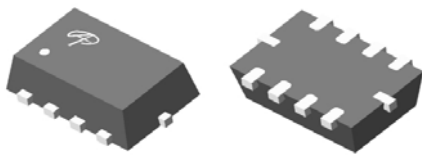
P-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

General Description

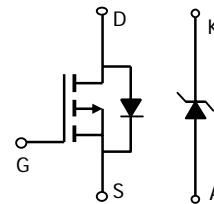
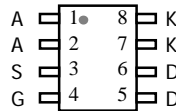
The AON4703 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. *Standard Product AON4703 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

V_{DS} (V) = -20V
 I_D = -3.4A (V_{GS} = -4.5V)
 $R_{DS(ON)}$ < 90m Ω (V_{GS} = -4.5V)
 $R_{DS(ON)}$ < 120m Ω (V_{GS} = -2.5V)
 $R_{DS(ON)}$ < 160m Ω (V_{GS} = -1.8V)
SCHOTTKY
 V_{KA} (V) = 20V, I_F = 1A, V_F < 0.5V@0.5A



DFN3X2-8L



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	± 8		V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	-3.4		A
	$T_A=70^\circ\text{C}$	-2.7		
Pulsed Drain Current ^B	I_{DM}	-15		
Schottky reverse voltage	V_{KA}		20	V
Continuous Forward Current ^A	$T_A=25^\circ\text{C}$		1.9	A
	$T_A=70^\circ\text{C}$		1.2	
Pulsed Forward Current ^B	I_{FM}		7	
Power Dissipation	$T_A=25^\circ\text{C}$	1.7	0.96	W
	$T_A=70^\circ\text{C}$	1.1	0.62	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Parameter: Thermal Characteristics MOSFET	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$	$R_{\theta JA}$	51	75	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A Steady-State		88	110	
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	28	35	
Thermal Characteristics Schottky				
Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$	$R_{\theta JA}$	66	80	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A Steady-State		95	130	
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	40	50	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	-0.63	-1	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-3.4A T _J =125°C		73 110	90 135	mΩ
		V _{GS} =-2.5V, I _D =-2.5A		99	120	mΩ
		V _{GS} =-1.8V, I _D =-1.5A		133	160	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3.4A	4	7		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.83	-1	V
I _S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		540		pF
C _{oss}	Output Capacitance			72		pF
C _{rss}	Reverse Transfer Capacitance			49		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-3.4A		6.1		nC
Q _{gs}	Gate Source Charge			0.6		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =2.9Ω, R _{GEN} =3Ω		10		ns
t _r	Turn-On Rise Time			12		ns
t _{D(off)}	Turn-Off DelayTime			44		ns
t _f	Turn-Off Fall Time			22		ns
t _{rr}	Body Diode Reverse Recovery Time		I _F =-3.4A, dI/dt=100A/μs		21	
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-3.4A, dI/dt=100A/μs		7.5		nC
SCHOTTKY PARAMETERS						
V _F	Forward Voltage Drop	I _F =0.5A		0.39	0.5	V
I _{rm}	Maximum reverse leakage current	V _R =5V			0.05	mA
		V _R =5V, T _J =125°C			10	
I _{rm}	Maximum reverse leakage current	V _R =16V			0.1	mA
		V _R =16V, T _J =125°C			20	
C _T	Junction Capacitance	V _R =10V		34		pF
t _{rr}	Schottky Reverse Recovery Time	I _F =1A, dI/dt=100A/μs		5.2	10	ns
Q _{rr}	Schottky Reverse Recovery Charge	I _F =1A, dI/dt=100A/μs		0.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t_{θJA} ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

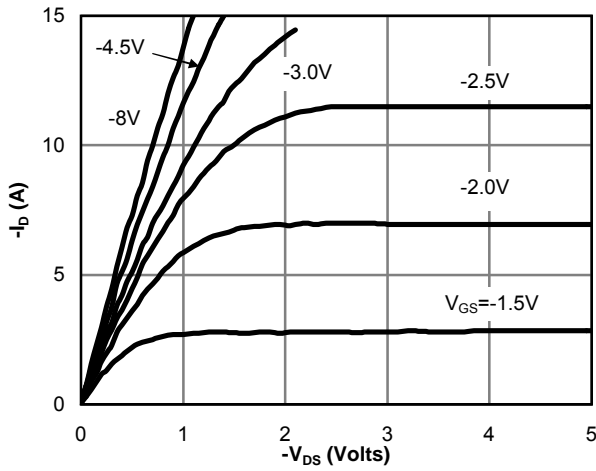


Fig 1: On-Region Characteristics

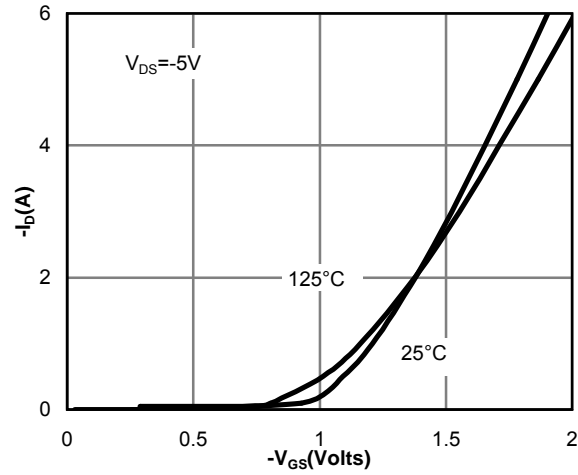


Figure 2: Transfer Characteristics

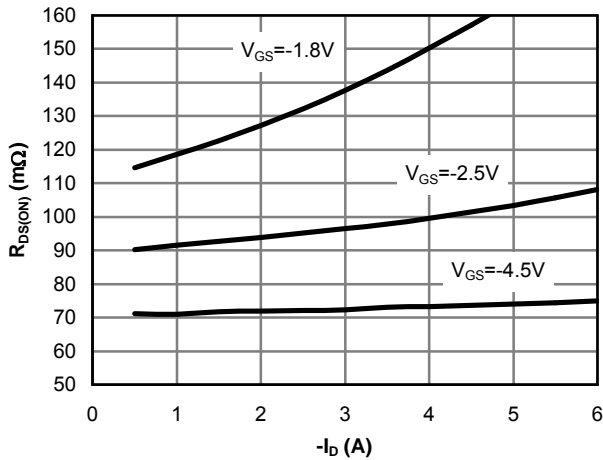


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

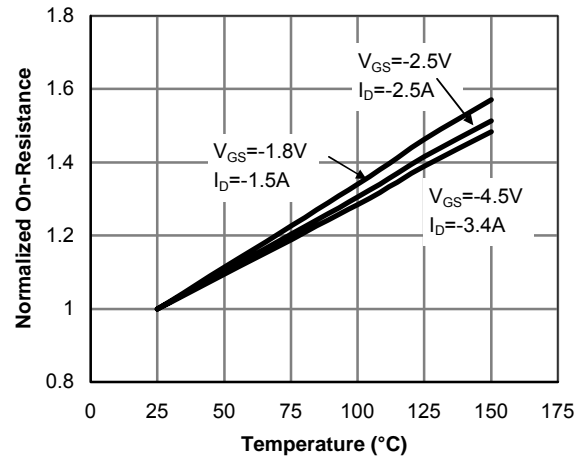


Figure 4: On-Resistance vs. Junction Temperature

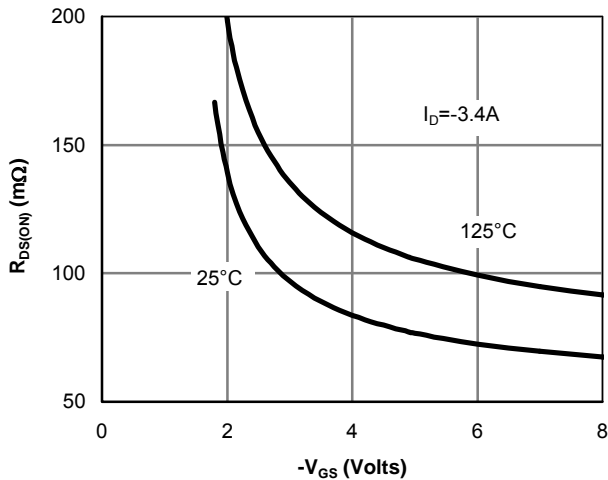


Figure 5: On-Resistance vs. Gate-Source Voltage

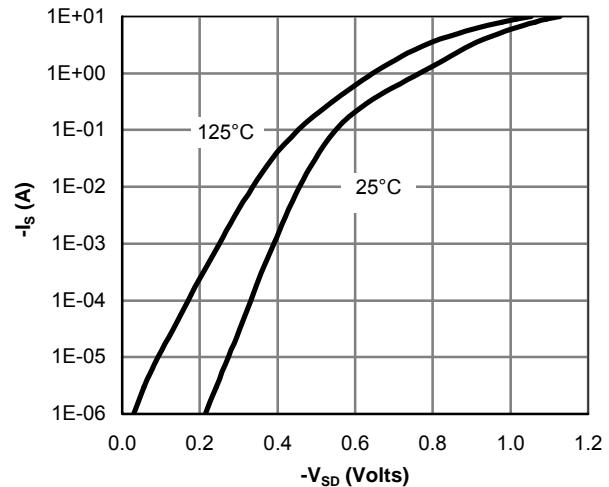


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

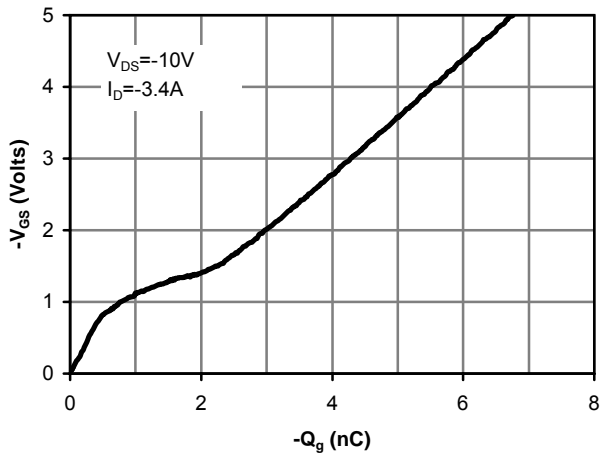


Figure 7: Gate-Charge Characteristics

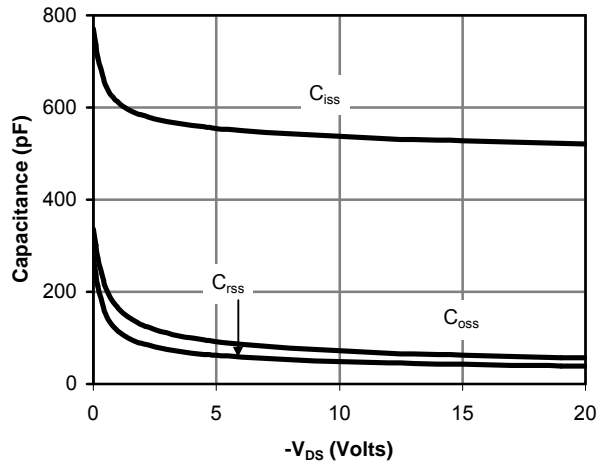


Figure 8: Capacitance Characteristics

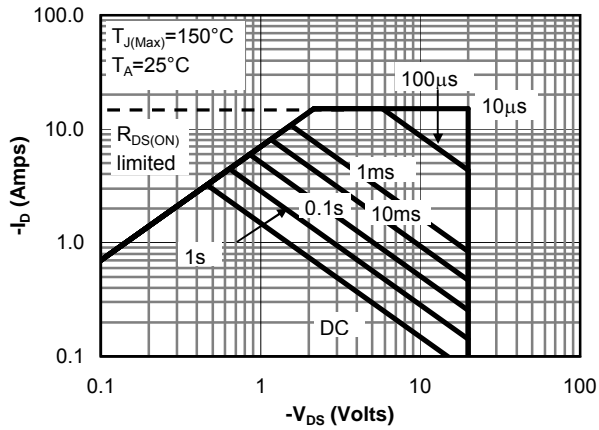


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

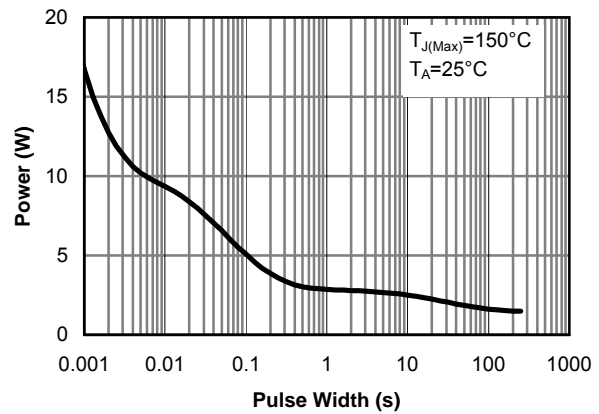


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

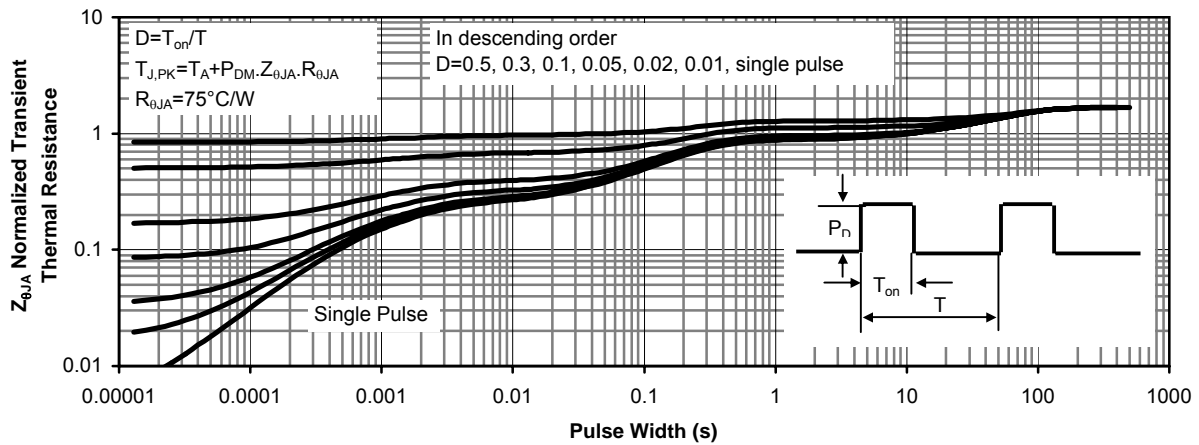


Figure 11: Normalized Maximum Transient Thermal Impedance